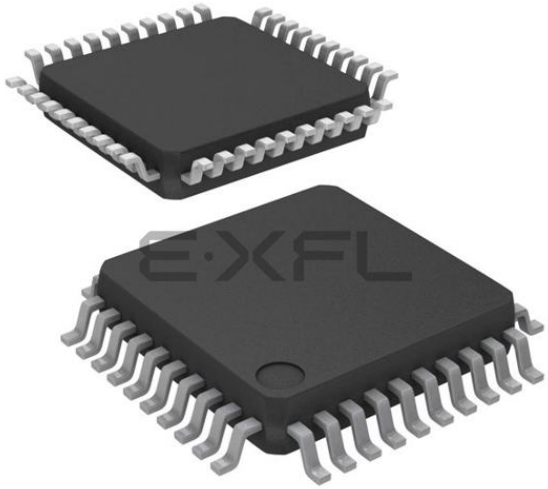
Renesas Electronics America Inc - R5F21336MNFP#V2 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	27
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21336mnfp-v2

1.1.2 Specifications

Tables 1.1 and 1.2 outline the Specifications for R8C/33M Group.

Table 1.1 Specifications for R8C/33M Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C CPU core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 1.8 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM, Data flash	Refer to **Table 1.3 Product List for R8C/33M Group**.
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3 (detection level of voltage detection 0 and voltage detection 1 selectable)
I/O Ports	Programmable I/O ports	• Input-only: 1 pin • CMOS I/O ports: 27, selectable pull-up resistor • High current drive ports: 27
Clock	Clock generation circuits	4 circuits: XIN clock oscillation circuit, XCIN clock oscillation circuit (32 kHz), High-speed on-chip oscillator (with frequency adjustment function), Low-speed on-chip oscillator • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• Number of interrupt vectors: 69 • External Interrupt: 7 ($\overline{\text{INT}}$ × 3, Key input × 4) • Priority levels: 7 levels
Watchdog Timer		• 14 bits × 1 (with prescaler) • Reset start selectable • Low-speed on-chip oscillator for watchdog timer selectable
DTC (Data Transfer Controller)		• 1 channel • Activation sources: 23 • Transfer modes: 2 (normal mode, repeat mode)
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode

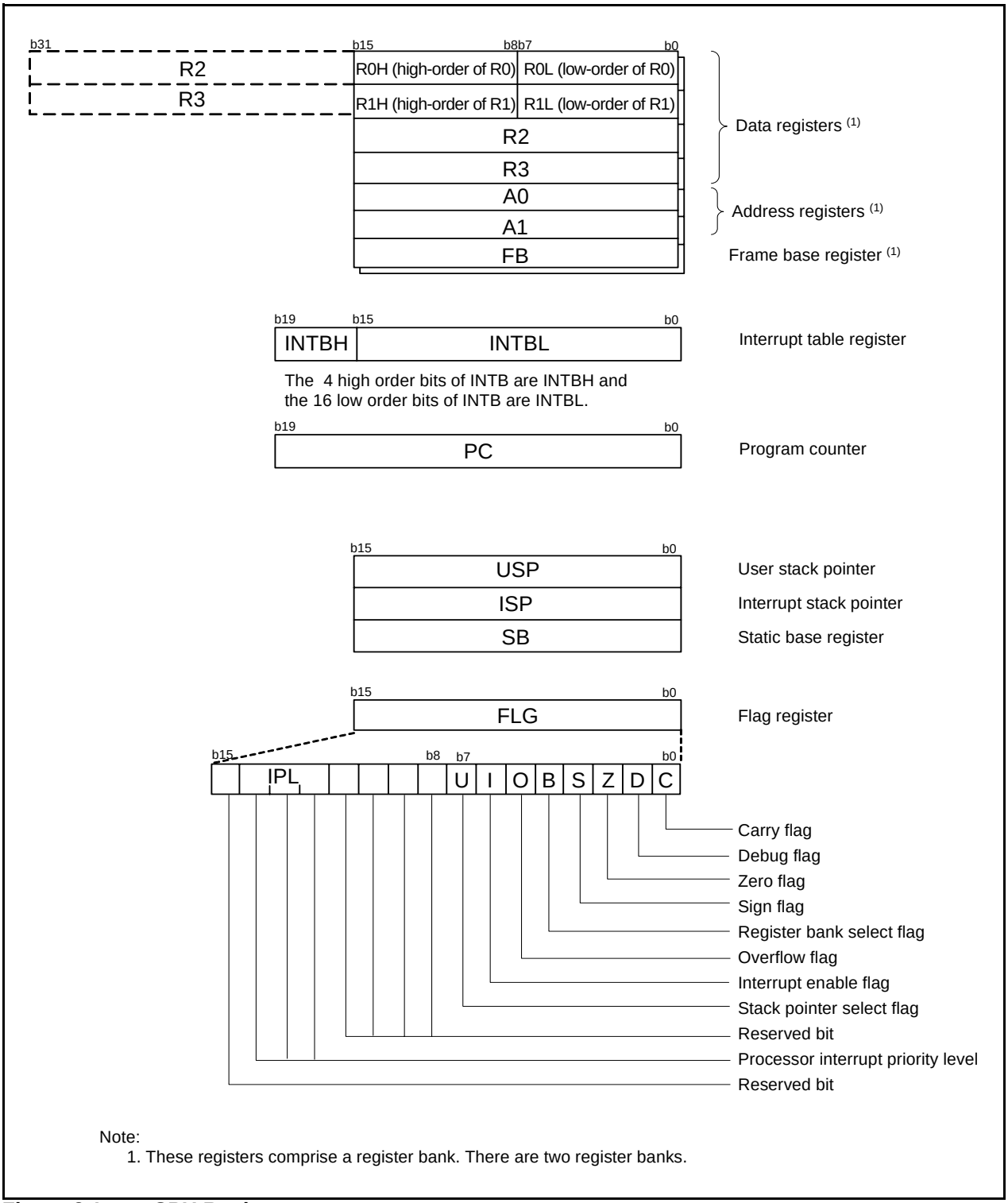
Table 1.4 Pin Name Information by Pin Number

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator A, Comparator B
1		P4_2						VREF
2	MODE							
3	$\overline{\text{RESET}}$							
4	XOUT(/XCOUT)	P4_7						
5	VSS/AVSS							
6	XIN(/XCIN)	P4_6						
7	VCC/AVCC							
8		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
9		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
10		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
11		P3_3	$\overline{\text{INT3}}$	(TRCCLK)	($\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$)	$\overline{\text{SCS}}$		IVCMP3
12		P2_2		(TRCIOD)				
13		P2_1		(TRCIOC)				
14		P2_0	($\overline{\text{INT1}}$)	(TRCIOB)				
15		P3_1		(TRBO)				
16		P4_5	$\overline{\text{INT0}}$		(RXD2/SCL2)			$\overline{\text{ADTRG}}$
17		P1_7	$\overline{\text{INT1}}$	(TRAIO)				IVCMP1
18		P1_6			(CLK0)			LVCOUT2/IVREF1
19		P1_5	($\overline{\text{INT1}}$)	(TRAIO)	(RXD0)			
20		P1_4		(TRCCLK)	(TXD0)			
21		P1_3	$\overline{\text{KI3}}$	TRBO (/TRCIOC)				AN11/LVCOUT1
22		P1_2	$\overline{\text{KI2}}$	(TRCIOB)				AN10/LVREF
23		P1_1	$\overline{\text{KI1}}$	(TRCIOA/ TRCTRG)				AN9/LVCMP2
24		P1_0	$\overline{\text{KI0}}$	(TRCIOD)				AN8/LVCMP1
25		P0_7		(TRCIOC)				AN0/DA1
26		P0_6		(TRCIOD)				AN1/DA0
27		P0_5		(TRCIOB)				AN2
28		P0_4		TREO (/TRCIOB)				AN3
29		P0_3		(TRCIOB)	(CLK1)			AN4
30		P0_2		(TRCIOA/ TRCTRG)	(RXD1)			AN5
31		P0_1		(TRCIOA/ TRCTRG)	(TXD1)			AN6
32		P0_0		(TRCIOA/ TRCTRG)				AN7

Note:
1. Can be assigned to the pin in parentheses by a program.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



Note:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the starting address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

Table 4.7 SFR Information (7) (1)

Address	Register	Symbol	After Reset
0180h	Timer RA Pin Select Register	TRASR	00h
0181h	Timer RB/RC Pin Select Register	TRBRCSR	00h
0182h	Timer RC Pin Select Register 0	TRCPSR0	00h
0183h	Timer RC Pin Select Register 1	TRCPSR1	00h
0184h			
0185h			
0186h			
0187h			
0188h	UART0 Pin Select Register	U0SR	00h
0189h	UART1 Pin Select Register	U1SR	00h
018Ah	UART2 Pin Select Register 0	U2SR0	00h
018Bh	UART2 Pin Select Register 1	U2SR1	00h
018Ch	SSU/IIC Pin Select Register	SSUIICSR	00h
018Dh			
018Eh	INT Interrupt Input Pin Select Register	INTSR	00h
018Fh	I/O Function Pin Select Register	PINSR	00h
0190h			
0191h			
0192h			
0193h	SS Bit Counter Register	SSBR	11111000b
0194h	SS Transmit Data Register L / IIC bus Transmit Data Register (2)	SSTDR / ICDRT	FFh
0195h	SS Transmit Data Register H (2)	SSTDRH	FFh
0196h	SS Receive Data Register L / IIC bus Receive Data Register (2)	SSRDR / ICDRR	FFh
0197h	SS Receive Data Register H (2)	SSRDRH	FFh
0198h	SS Control Register H / IIC bus Control Register 1 (2)	SSCRH / ICCR1	00h
0199h	SS Control Register L / IIC bus Control Register 2 (2)	SSCRL / ICCR2	01111101b
019Ah	SS Mode Register / IIC bus Mode Register (2)	SSMR / ICMR	00010000b / 00011000b
019Bh	SS Enable Register / IIC bus Interrupt Enable Register (2)	SSER / ICIER	00h
019Ch	SS Status Register / IIC bus Status Register (2)	SSSR / ICSR	00h / 0000X000b
019Dh	SS Mode Register 2 / Slave Address Register (2)	SSMR2 / SAR	00h
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h	Flash Memory Status Register	FST	10000X00b
01B3h			
01B4h	Flash Memory Control Register 0	FMR0	00h
01B5h	Flash Memory Control Register 1	FMR1	00h
01B6h	Flash Memory Control Register 2	FMR2	00h
01B7h			
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.12 SFR Information (12) (1)

Address	Register	Symbol	After Reset
2CF0h	DTC Control Data 22	DTCD22	XXh
2CF1h			XXh
2CF2h			XXh
2CF3h			XXh
2CF4h			XXh
2CF5h			XXh
2CF6h			XXh
2CF7h			XXh
2CF8h	DTC Control Data 23	DTCD23	XXh
2CF9h			XXh
2CFAh			XXh
2CFBh			XXh
2CFCh			XXh
2CFDh			XXh
2CFEh			XXh
2CFFh			XXh
2D00h			
:			
2FFFh			

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

Table 4.13 ID Code Areas and Option Function Select Area

Address	Area Name	Symbol	After Reset
:			
FFDBh	Option Function Select Register 2	OFS2	(Note 1)
:			
FFDFh	ID1		(Note 2)
:			
FFE3h	ID2		(Note 2)
:			
FFEBh	ID3		(Note 2)
:			
FFEFh	ID4		(Note 2)
:			
FFF3h	ID5		(Note 2)
:			
FFF7h	ID6		(Note 2)
:			
FFFBh	ID7		(Note 2)
:			
FFFFh	Option Function Select Register	OFS	(Note 1)

Notes:
1. The option function select area is allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
Do not write additions to the option function select area. If the block including the option function select area is erased, the option function select area is set to FFh.
When blank products are shipped, the option function select area is set to FFh. It is set to the written value after written by the user.
When factory-programming products are shipped, the value of the option function select area is the value programmed by the user.
2. The ID code areas are allocated in the flash memory, not in the SFRs. Set appropriate values as ROM data by a program.
Do not write additions to the ID code areas. If the block including the ID code areas is erased, the ID code areas are set to FFh.
When blank products are shipped, the ID code areas are set to FFh. They are set to the written value after written by the user.
When factory-programming products are shipped, the value of the ID code areas is the value programmed by the user.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	–40°C ≤ T_{opr} ≤ 85°C	500	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version) / –40 to 85 (D version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}		–	–	10	Bit
–	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	20	MHz
			3.2 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	16	MHz
			2.7 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	10	MHz
			2.2 ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	5	MHz
–	Tolerance level impedance				–	3	–	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
I_{Vref}	V_{ref} current		Vcc = 5 V, XIN = f1 = ϕAD = 20 MHz		–	45	–	µA
V_{ref}	Reference voltage				2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	–	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.7 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		1,000 (3)	–	–	times
–	Byte program time		–	80	500	µs
–	Block erase time		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5+CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time (7)	Ambient temperature = 55°C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.11 Voltage Detection 2 Circuit Electrical Characteristics

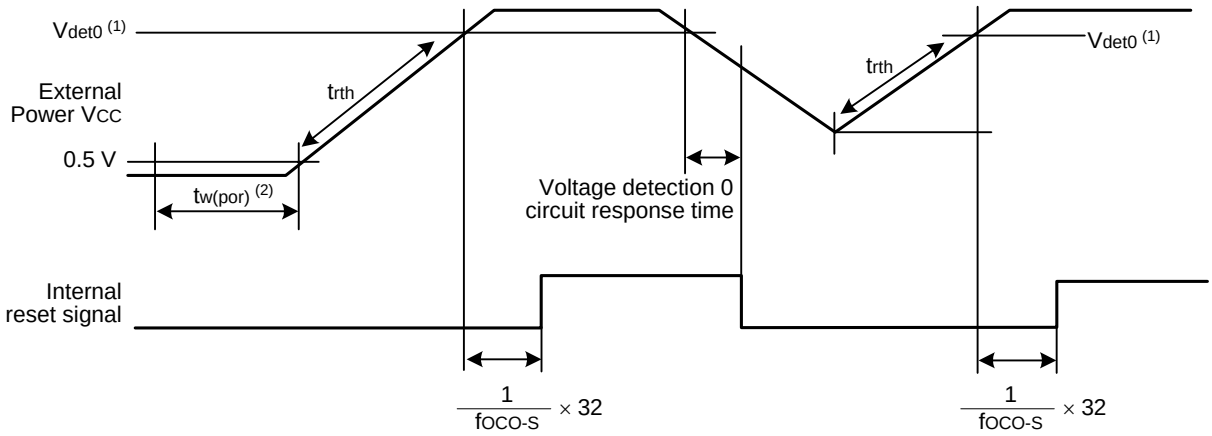
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0 (2)	At the falling of V_{CC}	3.70	4.00	4.30	V
	Voltage detection level Vdet2_EXT (2)	At the falling of LVCMP2	1.20	1.34	1.48	V
–	Hysteresis width at the rising of Vcc in voltage detection 2 circuit		–	0.10	–	V
–	Voltage detection 2 circuit response time (3)	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	20	150	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. The voltage detection level varies with detection targets. Select the level with the VCA24 bit in the VCA2 register.
3. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
4. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.12 Power-on Reset Circuit (2)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient	(1)	0	–	50,000	mV/ms

Notes:
1. The measurement condition is T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of User's Manual: Hardware for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.3 Power-on Reset Circuit Electrical Characteristics

Table 5.16 Timing Requirements of Synchronous Serial Communication Unit (SSU) (1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC} (2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC} (2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC} (2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	$1.5t_{CYC}$ + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	$1.5t_{CYC}$ + 200	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

Table 5.18 Electrical Characteristics (1) [4.2 V ≤ Vcc ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OH} = –20 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity Low V_{CC} = 5 V	I_{OH} = –5 mA	V_{CC} – 2.0	–	V_{CC}	V
		XOUT	V_{CC} = 5 V	I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity Low V_{CC} = 5 V	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	V_{CC} = 5 V	I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 5.0 V		0.1	1.2	–	V
		$\overline{RESET}$	V_{CC} = 5.0 V		0.1	1.2	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5.0 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5.0 V		–	–	–5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5.0 V		25	50	100	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 4.2 V ≤ V_{CC} ≤ 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.19 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.2	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	85	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	47	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Timing Requirements
(Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Topr = 25°C)

Table 5.20 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

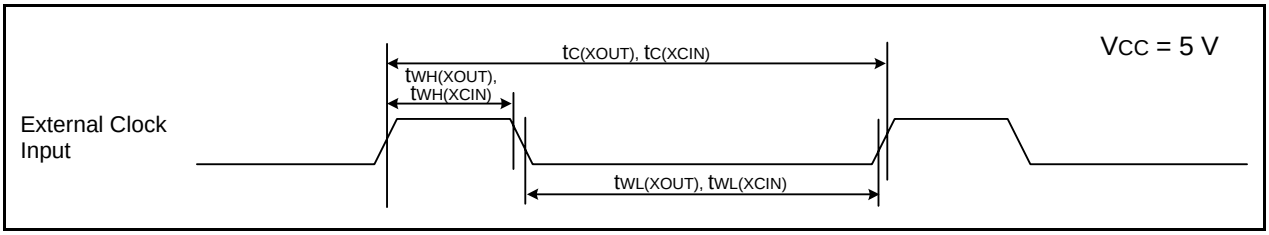


Figure 5.8 External Clock Input Timing Diagram when Vcc = 5 V

Table 5.21 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

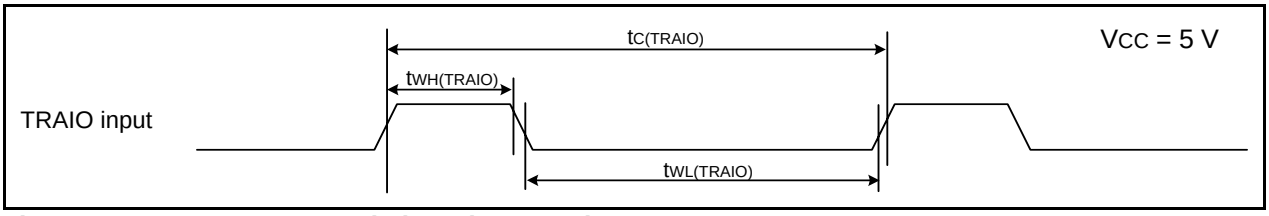


Figure 5.9 TRAIO Input Timing Diagram when Vcc = 5 V

Table 5.25 Electrical Characteristics (4) [2.7 V ≤ Vcc < 3.3 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.28 Serial Interface

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	When external clock is selected	300	–	ns
$t_{W(CKH)}$	CLKi input “H” width		150	–	ns
$t_{W(CKL)}$	CLKi Input “L” width		150	–	ns
$t_{d(C-Q)}$	TXDi output delay time		–	120	ns
$t_{h(C-Q)}$	TXDi hold time		0	–	ns
$t_{su(D-C)}$	RXDi input setup time		30	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns
$t_{d(C-Q)}$	TXDi output delay time	When internal clock is selected	–	30	ns
$t_{su(D-C)}$	RXDi input setup time		120	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns

i = 0 to 2

Note:

1. Vcc = 3 V and Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.

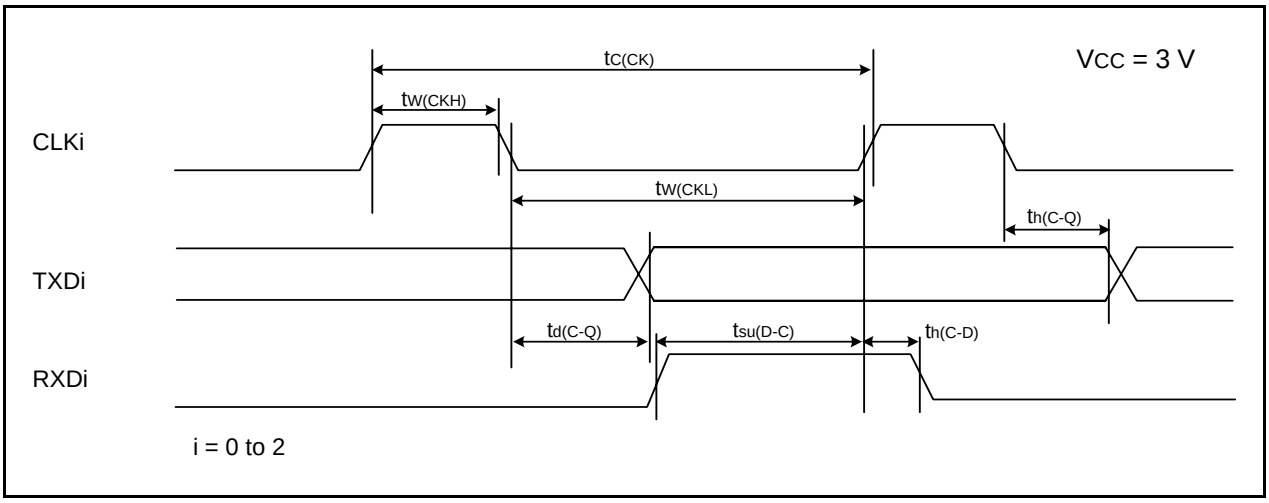


Figure 5.14 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.29 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	380 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	380 (2)	–	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

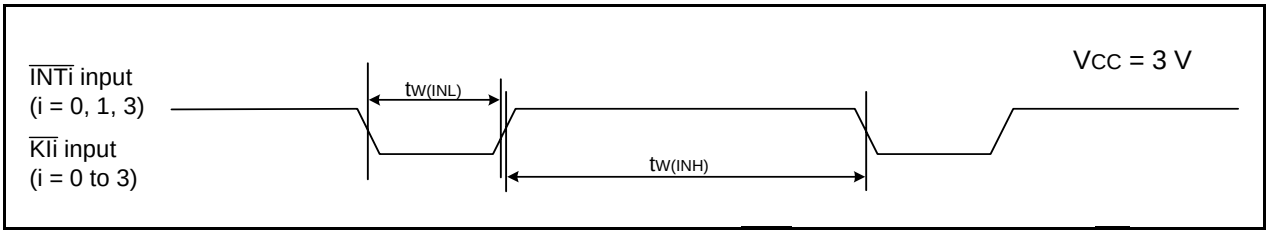


Figure 5.15 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 3 V

Table 5.30 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 µA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 2.2 V		0.05	0.20	–	V
		$\overline{RESET}$	V_{CC} = 2.2 V		0.05	0.2	–	V
I_{IH}	Input “H” current		VI = 2.2 V, V_{CC} = 2.2 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 2.2 V		–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 1.8 V ≤ V_{CC} < 2.7 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Table 5.31 Electrical Characteristics (6) [1.8 V ≤ Vcc < 2.7 V]
(Topr = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 1.8 to 2.7 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	2.2	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	0.8	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	2.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.7	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	–	80	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.34 Serial Interface

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	When external clock is selected	800	–	ns
$t_{W(CKH)}$	CLKi input “H” width		400	–	ns
$t_{W(CKL)}$	CLKi input “L” width		400	–	ns
$t_{d(C-Q)}$	TXDi output delay time		–	200	ns
$t_{h(C-Q)}$	TXDi hold time		0	–	ns
$t_{su(D-C)}$	RXDi input setup time		150	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns
$t_{d(C-Q)}$	TXDi output delay time	When internal clock is selected	–	200	ns
$t_{su(D-C)}$	RXDi input setup time		150	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns

i = 0 to 2

Note:

1. Vcc = 2.2 V and Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.

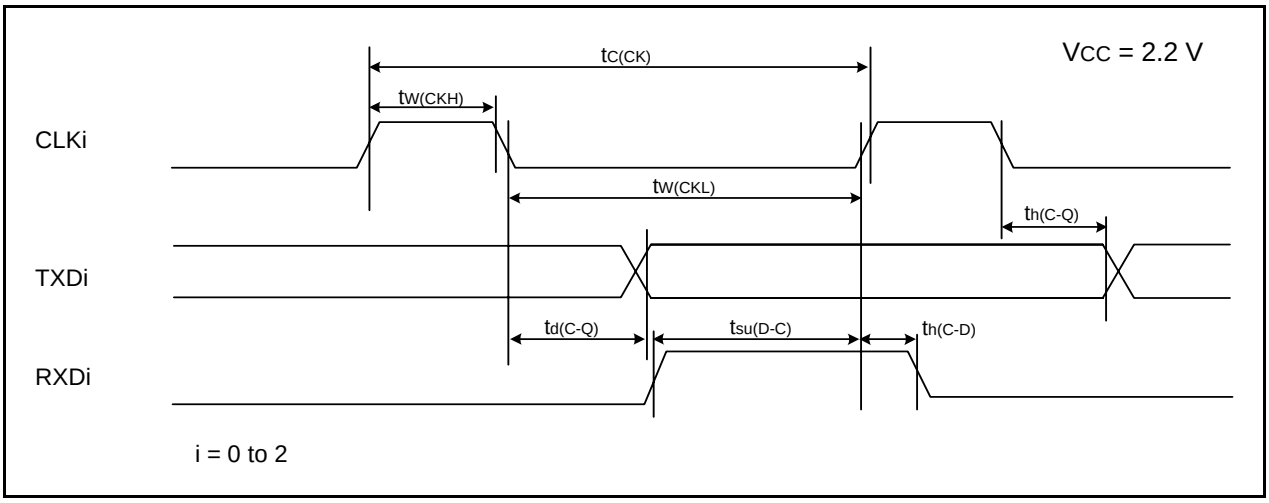


Figure 5.18 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.35 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	–	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

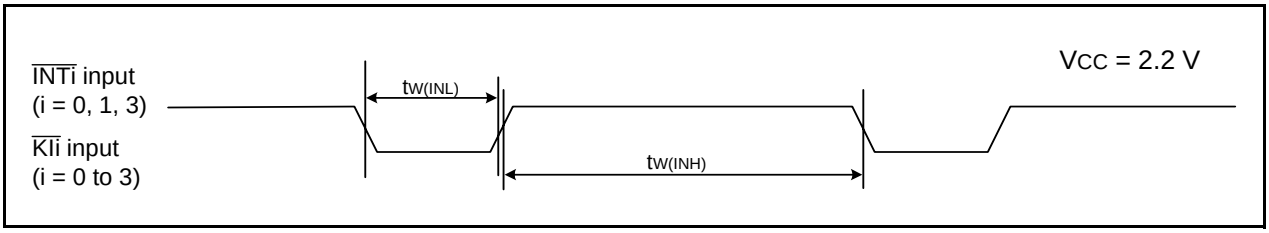


Figure 5.19 Input Timing Diagram for External Interrupt INTi and Key Input Interrupt KIi when Vcc = 2.2 V

General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

   Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

   — The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

   The state of the product is undefined at the moment when power is supplied.

   — The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

   In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

   In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

   Access to reserved addresses is prohibited.

   — The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

   After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

   — When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

5. Differences between Products

   Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

   — The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.